Yufeng Li

List of Publications by Year in descending order

26 papers	157 citations	1163117 8 h-index	1281871 11 g-index
26 all docs	26 docs citations	26 times ranked	255 citing authors

#	Article	IF	Citations
1	Phase transition filter from controllable hybrid line shape of correlation and squeezing of Pr3+: YPO4 and Eu3+: YPO4. Journal of Applied Physics, 2021, 130, .	2.5	1
2	Coherent Control of Multiphoton Using Multidressing Fields. Annalen Der Physik, 2021, 533, 2100083.	2.4	1
3	Phase transition and bandgap engineering in B1-Al N alloys: DFT calculations and experiments. Applied Surface Science, 2021, 575, 151641.	6.1	8
4	Demultiplexer of Multi-Order Correlation Interference in Nitrogen Vacancy Center Diamond. Materials, 2021, 14, 6745.	2.9	0
5	Resistance switching behaviors of continuous-thick hBN films fabricated by radio-frequency-sputtering. Journal of Materials Research, 2020, 35, 3247-3256.	2.6	8
6	GaN ultraviolet photodetector with petal-like Î²-Ga2O3 microcrystalline layer. AIP Advances, 2020, 10, .	1.3	4
7	Gas-sensing properties of ITO materials with different morphologies prepared by sputtering. SN Applied Sciences, 2020, 2, 1.	2.9	11
8	Indium tin oxide nanowires as voltage self-stabilizing supercapacitor electrodes. Journal of Materials Research, 2019, 34, 3195-3203.	2.6	5
9	InGaN microtube optical resonator with sub-wavelength wall thickness and its application to refractive index sensing. Journal of Applied Physics, 2019, 126, 075708.	2.5	4
10	Nanoscale Characterization of V-defect in InGaN/GaN QWs LEDs using Near-Field Scanning Optical Microscopy. Nanomaterials, 2019, 9, 633.	4.1	9
11	3D ITO-nanowire networks as transparent electrode for all-terrain substrate. Scientific Reports, 2019, 9, 4983.	3.3	5
12	Characteristics of GaN-based 500â€‰nm light-emitting diodes with embedded hemispherical air-cavity structure. Journal of Applied Physics, 2018, 123, 125702.	2.5	5
13	Heavily tin-doped indium oxide nano-pyramids as high-performance gas sensor. AIP Advances, 2018, 8, .	1.3	3
14	Three-Dimensional Anisotropic Microlaser from GaN-Based Self-Bent-Up Microdisk. ACS Photonics, 2018, 5, 4259-4264.	6.6	14
15	ITO nanowire networks coating on Âµ-hole arrayed substrate as super-broadband antireflection layer. Solar Energy, 2018, 173, 590-596.	6.1	4
16	Metamaterial study of quasi-three-dimensional bowtie nanoantennas at visible wavelengths. Scientific Reports, 2017, 7, 41966.	3.3	4
17	Fabrication and application of indium-tin-oxide nanowire networks by polystyrene-assisted growth. Scientific Reports, 2017, 7, 1600.	3.3	8
18	Controlled synthesis of polystyrene-assisted tin-doped indium oxide nanowire networks. Journal of Materials Research, 2017, 32, 1647-1655.	2.6	0

#	Article	IF	Citations
19	Efficiency droop suppression of distance-engineered surface plasmon-coupled photoluminescence in GaN-based quantum well LEDs. AIP Advances, 2017, 7, .	1.3	6
20	Whispering gallery mode lasing from InGaN/GaN quantum well microtube. Optics Express, 2017, 25, 18072.	3.4	15
21	Bipolar resistive switching behaviors of ITO nanowire networks. AIP Advances, 2016, 6, .	1.3	10
22	Growth and characterization of spindle-like Ga2O3 nanocrystals by electrochemical reaction in hydrofluoric solution. Applied Surface Science, 2016, 389, 205-210.	6.1	8
23	Electro-Optical Properties of Low-Temperature Growth Indium-tin-oxide Nanowires Using Polystyrene Spheres as Catalyst. Nanoscale Research Letters, 2016, 11, 131.	5.7	8
24	Time-resolved photoluminescence studies of InGaN/GaN multi-quantum-wells blue and green light-emitting diodes at room temperature. Optik, 2016, 127, 1809-1813.	2.9	7
25	ACU Enhancement of WLEDs Realized by Multilayer Phosphor With Convex Shape. IEEE Photonics Technology Letters, 2016, 28, 111-114.	2.5	5
26	Luminescence properties of InGaNâ€based dualâ€wavelength lightâ€emitting diodes with different quantumâ€well arrangements. Physica Status Solidi (A) Applications and Materials Science, 2015, 212, 954-959.	1.8	4